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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	102
Number of Gates	199000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50etc144-1

Similar to the FLEX 10KE architecture, embedded gate arrays are the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional "sea-of-gates" architecture. Additionally, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays reduce die area and increase speed when compared to standard gate arrays. While embedded megafunctions typically cannot be customized, FLEX 10KE devices are programmable, providing the designer with full control over embedded megafunctions and general logic, while facilitating iterative design changes during debugging.

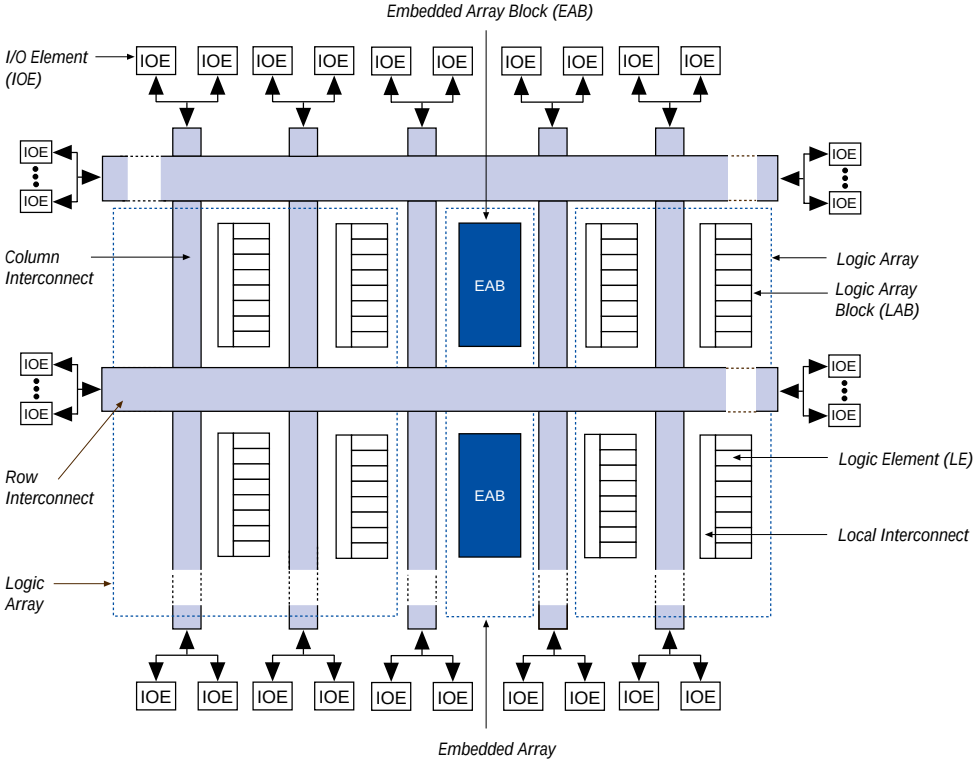
Each FLEX 10KE device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), wide data-path manipulation, microcontroller applications, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array and is used to implement general logic such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10KE devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, and EPC16 configuration devices, which configure FLEX 10KE devices via a serial data stream. Configuration data can also be downloaded from system RAM or via the Altera BitBlaster™, ByteBlasterMV™, or MasterBlaster download cables. After a FLEX 10KE device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 85 ms, real-time changes can be made during system operation.

FLEX 10KE devices contain an interface that permits microprocessors to configure FLEX 10KE devices serially or in-parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10KE device as memory and configure it by writing to a virtual memory location, making it easy to reconfigure the device.

Figure 1 shows a block diagram of the FLEX 10KE architecture. Each group of LEs is combined into an LAB; groups of LABs are arranged into rows and columns. Each row also contains a single EAB. The LABs and EABs are interconnected by the FastTrack Interconnect routing structure. IOEs are located at the end of each row and column of the FastTrack Interconnect routing structure.

Figure 1. FLEX 10KE Device Block Diagram



FLEX 10KE devices provide six dedicated inputs that drive the flipflops' control inputs and ensure the efficient distribution of high-speed, low-skew (less than 1.5 ns) control signals. These signals use dedicated routing channels that provide shorter delays and lower skews than the FastTrack Interconnect routing structure. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or an internally generated asynchronous clear signal that clears many registers in the device.

Embedded Array Block

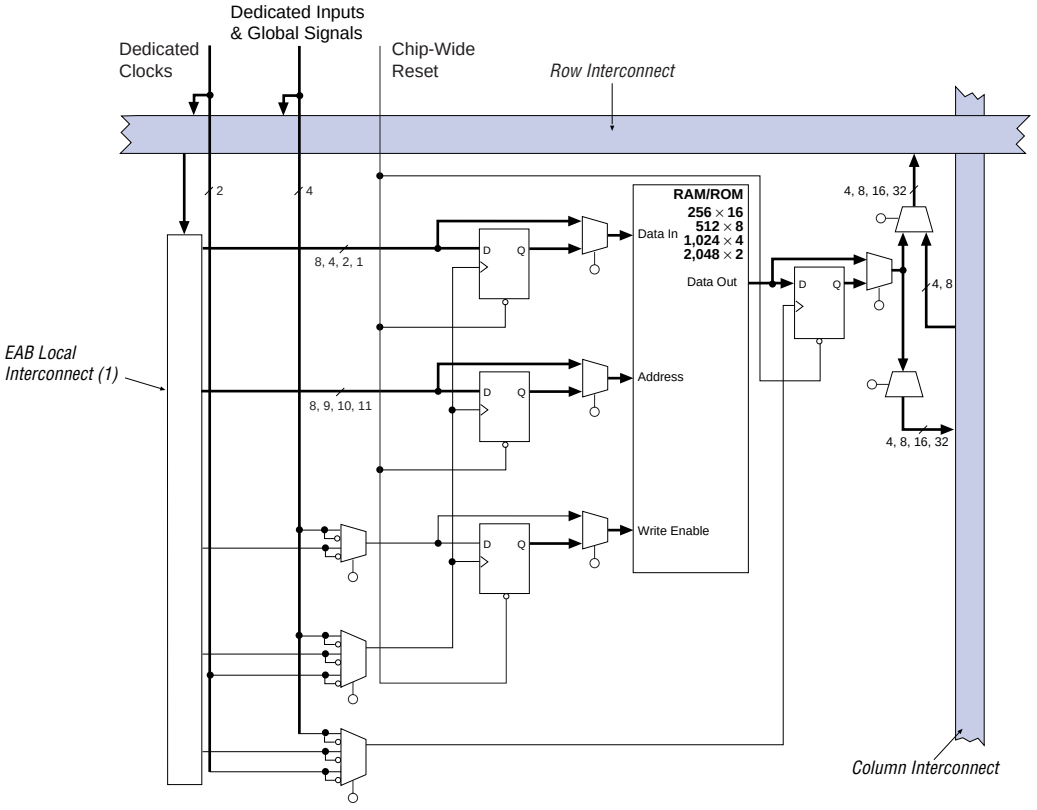
The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions such as LPM functions can take advantage of the EAB automatically.

The FLEX 10KE EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These small FPGA RAM blocks must be connected together to make RAM blocks of manageable size. The RAM blocks are connected together using multiplexers implemented with more logic blocks. These extra multiplexers cause extra delay, which slows down the RAM block. FPGA RAM blocks are also prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

The FLEX 10KE enhanced EAB adds dual-port capability to the existing EAB structure. The dual-port structure is ideal for FIFO buffers with one or two clocks. The FLEX 10KE EAB can also support up to 16-bit-wide RAM blocks and is backward-compatible with any design containing FLEX 10K EABs. The FLEX 10KE EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, which allows the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

Figure 4. FLEX 10KE Device in Single-Port RAM Mode



Note:

(1) EPF10K30E, EPF10K50E, and EPF10K50S devices have 88 EAB local interconnect channels; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 104 EAB local interconnect channels.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the write enable signal. In contrast, the EAB's synchronous RAM generates its own write enable signal and is self-timed with respect to the input or write clock. A circuit using the EAB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

Cascade Chain

With the cascade chain, the FLEX 10KE architecture can implement functions that have a very wide fan-in. Adjacent LUTs can be used to compute portions of the function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical AND or logical OR (via De Morgan's inversion) to connect the outputs of adjacent LEs. An a delay as low as 0.6 ns per LE, each additional LE provides four more inputs to the effective width of a function. Cascade chain logic can be created automatically by the Altera Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than eight bits are implemented automatically by linking several LABs together. For easier routing, a long cascade chain skips every other LAB in a row. A cascade chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB (e.g., the last LE of the first LAB in a row cascades to the first LE of the third LAB). The cascade chain does not cross the center of the row (e.g., in the EPF10K50E device, the cascade chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB). This break is due to the EAB's placement in the middle of the row.

Figure 10 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in. These examples show functions of 4*n* variables implemented with *n* LEs. The LE delay is 0.9 ns; the cascade chain delay is 0.6 ns. With the cascade chain, 2.7 ns are needed to decode a 16-bit address.

Figure 10. FLEX 10KE Cascade Chain Operation

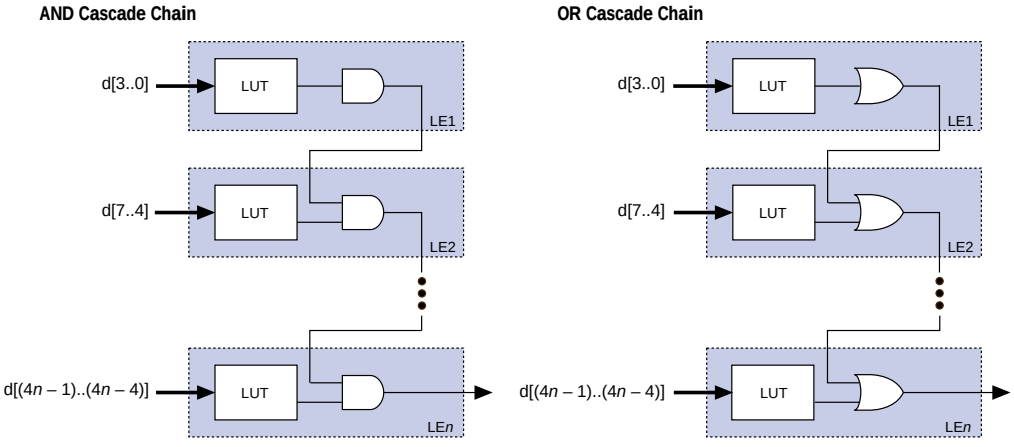
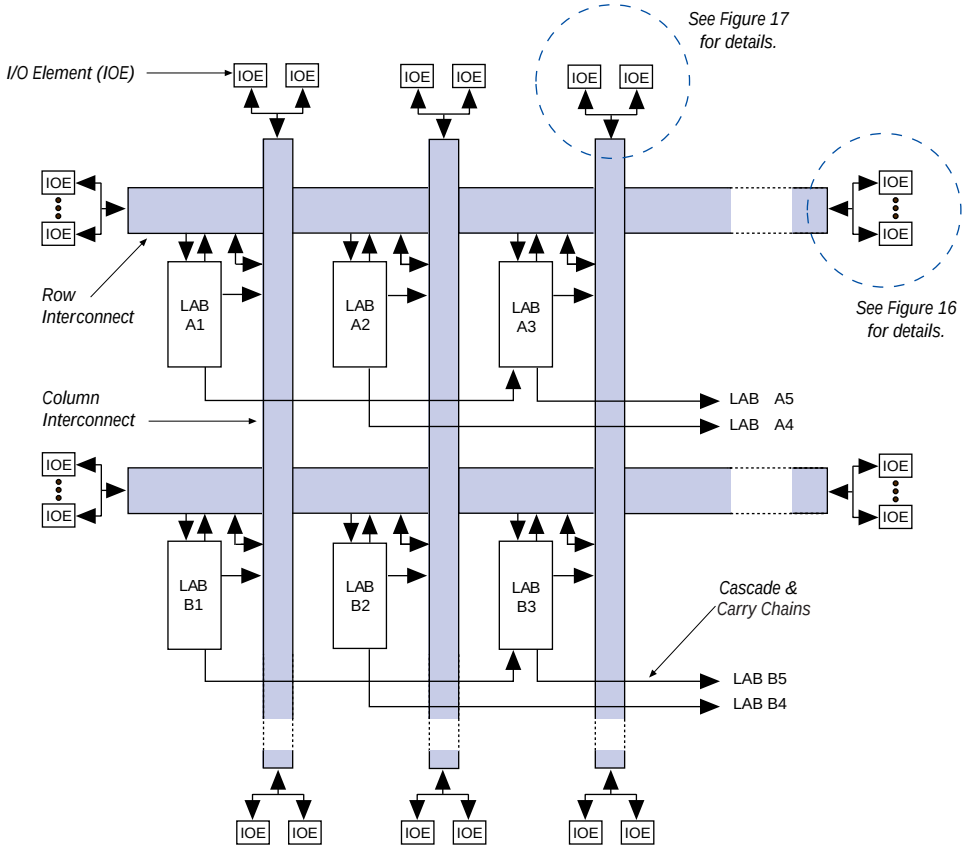


Figure 14. FLEX 10KE Interconnect Resources



I/O Element

An IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data that requires a fast setup time, or as an output register for data that requires fast clock-to-output performance. In some cases, using an LE register for an input register will result in a faster setup time than using an IOE register. IOEs can be used as input, output, or bidirectional pins. For bidirectional registered I/O implementation, the output register should be in the IOE, and the data input and output enable registers should be LE registers placed adjacent to the bidirectional pin. The Altera Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Figure 15 shows the bidirectional I/O registers.

On all FLEX 10KE devices (except EPF10K50E and EPF10K200E devices), the input path from the I/O pad to the FastTrack Interconnect has a programmable delay element that can be used to guarantee a zero hold time. EPF10K50S and EPF10K200S devices also support this feature. Depending on the placement of the IOE relative to what it is driving, the designer may choose to turn on the programmable delay to ensure a zero hold time or turn it off to minimize setup time. This feature is used to reduce setup time for complex pin-to-register paths (e.g., PCI designs).

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across the device and provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, a LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal resets all IOE registers, overriding any other control signals.

When a dedicated clock pin drives IOE registers, it can be inverted for all IOEs in the device. All IOEs must use the same sense of the clock. For example, if any IOE uses the inverted clock, all IOEs must use the inverted clock and no IOE can use the non-inverted clock. However, LEs can still use the true or complement of the clock on a LAB-by-LAB basis.

The incoming signal may be inverted at the dedicated clock pin and will drive all IOEs. For the true and complement of a clock to be used to drive IOEs, drive it into both global clock pins. One global clock pin will supply the true, and the other will supply the complement.

When the true and complement of a dedicated input drives IOE clocks, two signals on the peripheral control bus are consumed, one for each sense of the clock.

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels is different for each IOE (see Figure 17).

Figure 17. FLEX 10KE Column-to-IOE Connections

The values for m and n are provided in Table 11.

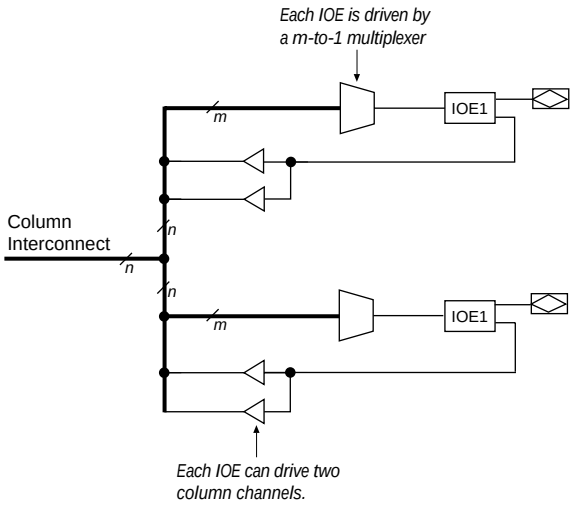


Table 11 lists the FLEX 10KE column-to-IOE interconnect resources.

Table 11. FLEX 10KE Column-to-IOE Interconnect Resources

Device	Channels per Column *(n)*	Column Channels per Pin *(m)*
EPF10K30E	24	16
EPF10K50E EPF10K50S	24	16
EPF10K100E	24	16
EPF10K130E	32	24
EPF10K200E EPF10K200S	48	40

Table 23. FLEX 10KE Device Capacitance *Note (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input voltage is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(6) Typical values are for T_A = 25° C, V_{CCINT} = 2.5 V, and V_{CCIO} = 2.5 V or 3.3 V.
(7) These values are specified under the FLEX 10KE Recommended Operating Conditions shown in Tables 20 and 21.
(8) The FLEX 10KE input buffers are compatible with 2.5-V, 3.3-V (LVTTL and LVCMOS), and 5.0-V TTL and CMOS signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in Figure 22.
(9) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(10) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(11) This value is specified for normal device operation. The value may vary during power-up.
(12) This parameter applies to -1 speed-grade commercial-temperature devices and -2 speed-grade-industrial temperature devices.
(13) Pin pull-up resistance values will be lower if the pin is driven higher than V_{CCIO} by an external source.
(14) Capacitance is sample-tested only.

Figure 25. FLEX 10KE Device LE Timing Model

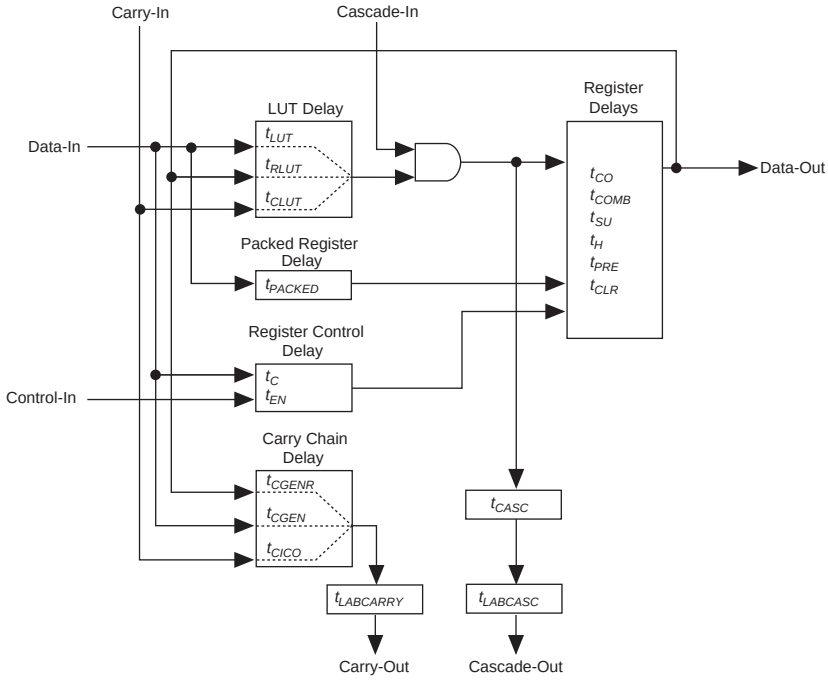


Table 24. LE Timing Microparameters (Part 2 of 2) *Note (1)*		
Symbol	**Parameter**	**Condition**
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 25. IOE Timing Microparameters *Note (1)*		
Symbol	**Parameter**	**Conditions**
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 33. EPF10K30E Device EAB Internal Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.7		2.0		2.3	ns
$t_{EABDATA1}$		0.6		0.7		0.8	ns
t_{EABWE1}		1.1		1.3		1.4	ns
t_{EABWE2}		0.4		0.4		0.5	ns
t_{EABRE1}		0.8		0.9		1.0	ns
t_{EABRE2}		0.4		0.4		0.5	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.3		0.4	ns
$t_{EABBYPASS}$		0.5		0.6		0.7	ns
t_{EABSU}	0.9		1.0		1.2		ns
t_{EABH}	0.4		0.4		0.5		ns
t_{EABCLR}	0.3		0.3		0.3		ns
t_{AA}		3.2		3.8		4.4	ns
t_{WP}	2.5		2.9		3.3		ns
t_{RP}	0.9		1.1		1.2		ns
t_{WDSU}	0.9		1.0		1.1		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.7		2.0		2.3		ns
t_{WAH}	1.8		2.1		2.4		ns
t_{RASU}	3.1		3.7		4.2		ns
t_{RAH}	0.2		0.2		0.2		ns
t_{WO}		2.5		2.9		3.3	ns
t_{DD}		2.5		2.9		3.3	ns
t_{EABOUT}		0.5		0.6		0.7	ns
t_{EABCH}	1.5		2.0		2.3		ns
t_{EABCL}	2.5		2.9		3.3		ns

Table 37. EPF10K30E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (3)	2.8		3.9		5.2		ns
$t_{INHBIDIR}$ (3)	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ (4)	3.8		4.9		–		ns
$t_{INHBIDIR}$ (4)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns
$t_{XZBIDIR}$ (3)		6.1		7.5		9.7	ns
$t_{ZXBIDIR}$ (3)		6.1		7.5		9.7	ns
$t_{OUTCOBIDIR}$ (4)	0.5	3.9	0.5	4.9	–	–	ns
$t_{XZBIDIR}$ (4)		5.1		6.5		–	ns
$t_{ZXBIDIR}$ (4)		5.1		6.5		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 38 through 44 show EPF10K50E device internal and external timing parameters.

Table 38. EPF10K50E Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.9		1.3	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.7		0.8		1.1	ns
t_{PACKED}		0.4		0.5		0.6	ns
t_{EN}		0.6		0.7		0.9	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.5		0.5		0.8	ns
t_{CGENR}		0.2		0.2		0.3	ns
t_{CASC}		0.8		1.0		1.4	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.7		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.8	ns
t_{SU}	0.7		0.7		0.8		ns

Table 48. EPF10K100E Device EAB Internal Timing Macroparameters *(Part 2 of 2)* *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABWCOMB}$	5.9		7.7		10.3		ns
$t_{EABWCREG}$	5.4		7.0		9.4		ns
t_{EABDD}		3.4		4.5		5.9	ns
$t_{EABDATACO}$		0.5		0.7		0.8	ns
$t_{EABDATASU}$	0.8		1.0		1.4		ns
$t_{EABDATAH}$	0.1		0.1		0.2		ns
$t_{EABWESU}$	1.1		1.4		1.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.0		1.3		1.7		ns
t_{EABWDH}	0.2		0.2		0.3		ns
$t_{EABWASU}$	4.1		5.2		6.8		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		3.4		4.5		5.9	ns

Table 49. EPF10K100E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.6		4.4	ns
t_{DIN2LE}		0.3		0.4		0.5	ns
$t_{DIN2DATA}$		1.6		1.8		2.0	ns
$t_{DCLK2IOE}$		0.8		1.1		1.4	ns
$t_{DCLK2LE}$		0.3		0.4		0.5	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		2.5		3.4	ns
$t_{SAMECOLUMN}$		0.4		1.0		1.6	ns
$t_{DIFFROW}$		1.9		3.5		5.0	ns
$t_{TWOROWS}$		3.4		6.0		8.4	ns
$t_{LEPERIPH}$		4.3		5.4		6.5	ns
$t_{LABCARRY}$		0.5		0.7		0.9	ns
$t_{LABCASC}$		0.8		1.0		1.4	ns

Table 53. EPF10K130E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{OD3}		4.0		5.6		7.5	ns
t_{XZ}		2.8		4.1		5.5	ns
t_{ZX1}		2.8		4.1		5.5	ns
t_{ZX2}		2.8		4.1		5.5	ns
t_{ZX3}		4.0		5.6		7.5	ns
t_{INREG}		2.5		3.0		4.1	ns
t_{IOFD}		0.4		0.5		0.6	ns
t_{INCOMB}		0.4		0.5		0.6	ns

Table 54. EPF10K130E Device EAB Internal Microparameters *(Part 1 of 2)* *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		2.0		2.6	ns
$t_{EABDATA2}$		0.0		0.0		0.0	ns
t_{EABWE1}		1.5		2.0		2.6	ns
t_{EABWE2}		0.3		0.4		0.5	ns
t_{EABRE1}		0.3		0.4		0.5	ns
t_{EABRE2}		0.0		0.0		0.0	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.4		0.5	ns
$t_{EABBYPASS}$		0.1		0.1		0.2	ns
t_{EABSU}	0.8		1.0		1.4		ns
t_{EABH}	0.1		0.2		0.2		ns
t_{EABCLR}	0.3		0.4		0.5		ns
t_{AA}		4.0		5.0		6.6	ns
t_{WP}	2.7		3.5		4.7		ns
t_{RP}	1.0		1.3		1.7		ns
t_{WDSU}	1.0		1.3		1.7		ns
t_{WDH}	0.2		0.2		0.3		ns
t_{WASU}	1.6		2.1		2.8		ns
t_{WAH}	1.6		2.1		2.8		ns
t_{RASU}	3.0		3.9		5.2		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		1.5		2.0		2.6	ns

Table 56. EPF10K130E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		2.8		3.5		4.4	ns
t_{DIN2LE}		0.7		1.2		1.6	ns
$t_{DIN2DATA}$		1.6		1.9		2.2	ns
$t_{DCLK2IOE}$		1.6		2.1		2.7	ns
$t_{DCLK2LE}$		0.7		1.2		1.6	ns
$t_{SAMELAB}$		0.1		0.2		0.2	ns
$t_{SAMEROW}$		1.9		3.4		5.1	ns
$t_{SAMECOLUMN}$		0.9		2.6		4.4	ns
$t_{DIFFROW}$		2.8		6.0		9.5	ns
$t_{TWOROWS}$		4.7		9.4		14.6	ns
$t_{LEPERIPH}$		3.1		4.7		6.9	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.9		1.2		1.6	ns

Table 57. EPF10K130E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	1.9		2.1		3.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.0	2.0	7.0	2.0	9.2	ns
t_{INSU} *(4)*	0.9		1.1		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	4.0	0.5	6.0	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 59. EPF10K200E Device LE Timing Microparameters *(Part 2 of 2)* *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_H	0.9		1.1		1.5		ns
t_{PRE}		0.5		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 60. EPF10K200E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.6		1.9		2.6	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		1.6		1.9		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		0.9		1.2		ns
t_{IOH}	0.7		0.8		1.1		ns
t_{IOCLR}		0.2		0.2		0.3	ns
t_{OD1}		0.6		0.7		0.9	ns
t_{OD2}		0.1		0.2		0.7	ns
t_{OD3}		2.5		3.0		3.9	ns
t_{XZ}		4.4		5.3		7.1	ns
t_{ZX1}		4.4		5.3		7.1	ns
t_{ZX2}		3.9		4.8		6.9	ns
t_{ZX3}		6.3		7.6		10.1	ns
t_{INREG}		4.8		5.7		7.7	ns
t_{IOFD}		1.5		1.8		2.4	ns
t_{INCOMB}		1.5		1.8		2.4	ns

Table 61. EPF10K200E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		2.0		2.4		3.2	ns
$t_{EABDATA1}$		0.4		0.5		0.6	ns
t_{EABWE1}		1.4		1.7		2.3	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0		0		0	ns
t_{EABRE2}		0.4		0.5		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		0.9		1.2	ns
$t_{EABBYPASS}$		0.0		0.1		0.1	ns
t_{EABSU}	0.9		1.1		1.5		ns
t_{EABH}	0.4		0.5		0.6		ns
t_{EABCLR}	0.8		0.9		1.2		ns
t_{AA}		3.1		3.7		4.9	ns
t_{WP}	3.3		4.0		5.3		ns
t_{RP}	0.9		1.1		1.5		ns
t_{WDSU}	0.9		1.1		1.5		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.3		1.6		2.1		ns
t_{WAH}	2.1		2.5		3.3		ns
t_{RASU}	2.2		2.6		3.5		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		2.0		2.4		3.2	ns
t_{DD}		2.0		2.4		3.2	ns
t_{EABOUT}		0.0		0.1		0.1	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	3.3		4.0		5.3		ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		5.1		6.4		8.4	ns
$t_{EABRCOMB}$	5.1		6.4		8.4		ns
$t_{EABRCREG}$	4.8		5.7		7.6		ns
t_{EABWP}	3.3		4.0		5.3		ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABWCOMB}$	6.7		8.1		10.7		ns
$t_{EABWCREG}$	6.6		8.0		10.6		ns
t_{EABDD}		4.0		5.1		6.7	ns
$t_{EABDATACO}$		0.8		1.0		1.3	ns
$t_{EABDATASU}$	1.3		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.9		1.1		1.5		ns
t_{EABWEH}	0.4		0.5		0.6		ns
$t_{EABWDSU}$	1.5		1.8		2.4		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.7		ns
t_{EABWAH}	0.4		0.5		0.7		ns
t_{EABWO}		3.4		4.4		5.8	ns

Table 63. EPF10K200E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.2		4.6		5.7	ns
t_{DIN2LE}		1.7		1.7		2.0	ns
$t_{DIN2DATA}$		1.9		2.1		3.0	ns
$t_{DCLK2IOE}$		2.5		2.9		4.0	ns
$t_{DCLK2LE}$		1.7		1.7		2.0	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.3		2.6		3.6	ns
$t_{SAMECOLUMN}$		2.5		2.7		4.1	ns
$t_{DIFFROW}$		4.8		5.3		7.7	ns
$t_{TWOROWS}$		7.1		7.9		11.3	ns
$t_{LEPERIPH}$		7.0		7.6		9.0	ns
$t_{LABCARRY}$		0.1		0.1		0.2	ns
$t_{LABCASC}$		0.9		1.0		1.4	ns

Table 69. EPF10K50S Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		3.7		5.2		7.0	ns
$t_{EABRCCOMB}$	3.7		5.2		7.0		ns
$t_{EABRCREG}$	3.5		4.9		6.6		ns
t_{EABWP}	2.0		2.8		3.8		ns
$t_{EABWCCOMB}$	4.5		6.3		8.6		ns
$t_{EABWCREG}$	5.6		7.8		10.6		ns
t_{EABDD}		3.8		5.3		7.2	ns
$t_{EABDATACO}$		0.8		1.1		1.5	ns
$t_{EABDATASU}$	1.1		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.7		1.0		1.3		ns
t_{EABWEH}	0.4		0.6		0.8		ns
$t_{EABWDSU}$	1.2		1.7		2.2		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.6		2.3		3.0		ns
t_{EABWAH}	0.9		1.2		1.8		ns
t_{EABWO}		3.1		4.3		5.9	ns

Table 70. EPF10K50S Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.7		4.6	ns
t_{DIN2LE}		1.7		2.1		2.7	ns
$t_{DIN2DATA}$		2.7		3.1		5.1	ns
$t_{DCLK2IOE}$		1.6		1.9		2.6	ns
$t_{DCLK2LE}$		1.7		2.1		2.7	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		1.7		2.4	ns
$t_{SAMECOLUMN}$		1.0		1.3		2.1	ns
$t_{DIFFROW}$		2.5		3.0		4.5	ns
$t_{TWOROWS}$		4.0		4.7		6.9	ns
$t_{LEPERIPH}$		2.6		2.9		3.4	ns
$t_{LABCARRY}$		0.1		0.2		0.2	ns
$t_{LABCASC}$		0.8		1.0		1.3	ns